

ESDB0511P

Transient Voltage Suppressors

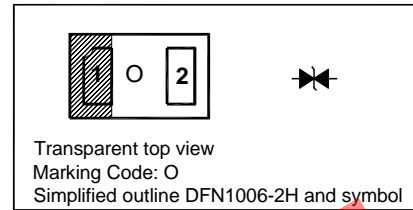
for ESD Protection

Features

- Low Clamping Voltage
- Low Leakage current
- Protects one I/O or power line
- Bi-direction high reliability

PINNING

PIN	DESCRIPTION
1	Anode
2	Anode

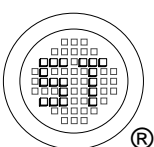


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
IEC61000-4-2 (ESD) Air Contact	V_{ESD}	± 15 ± 8	KV
Peak Pulse Current ($t_p = 8/20 \mu\text{s}$)	I_{PP}	12	A
Peak Pulse Power ($t_p = 8/20 \mu\text{s}$)	P_{pk}	170	W
Junction Temperature	T_j	- 55 to + 125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

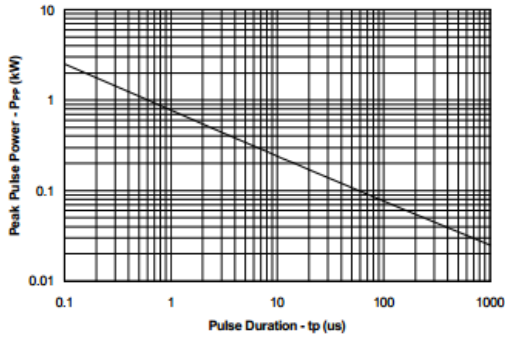
Type	Reverse Stand-off Voltage	Reverse Current	Breakdown Voltage			Clamping Voltage	Reverse Peak Pulse Current	Capacitance		
	V_{RWM}	I_R at V_{RWM}	V_{BR}		at I_T	V_C at I_{PP}	I_{PP}	C_j	at f	at V_R
	Max. (V)	Max. (μA)	Min. (V)	Max. (V)	(mA)	Max. (V)	(A)	Max. (pF)	(MHz)	(V)
ESDB0511P	5	1	6	10	1	11	1	75	1	0
						14	12			



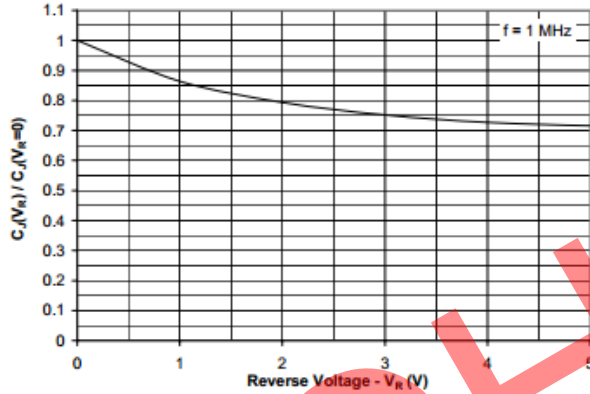
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Non-Repetitive Peak Pulse Power vs. Pulse Time



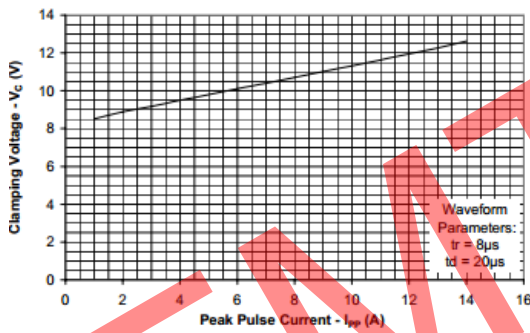
Junction Capacitance vs. Reverse Voltage



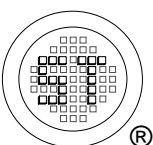
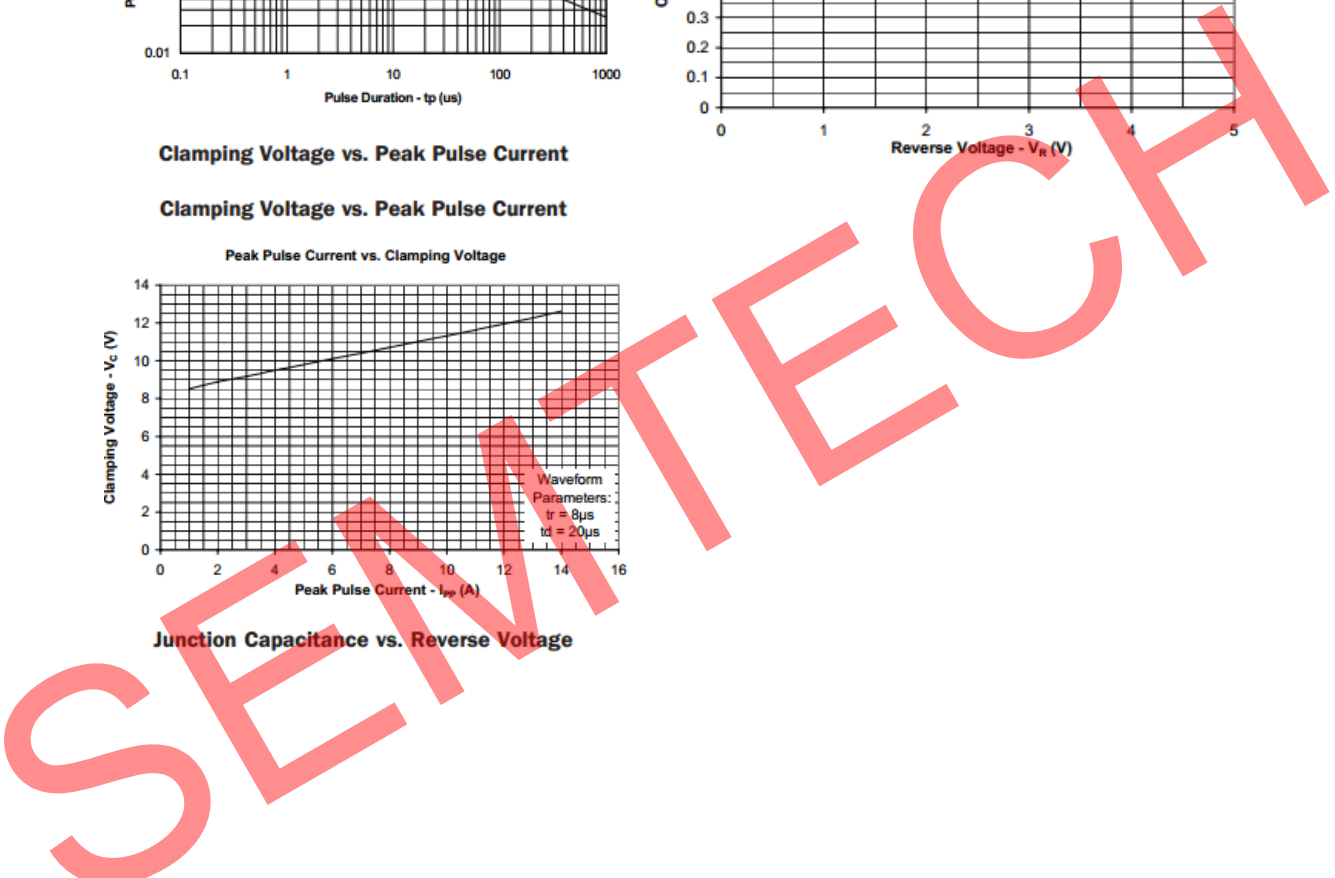
Clamping Voltage vs. Peak Pulse Current

Clamping Voltage vs. Peak Pulse Current

Peak Pulse Current vs. Clamping Voltage



Junction Capacitance vs. Reverse Voltage



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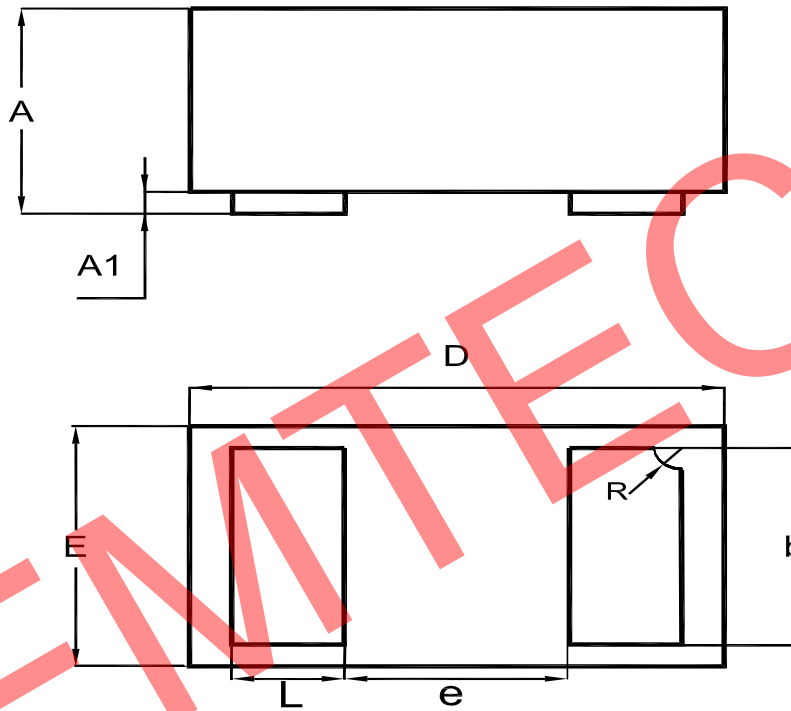


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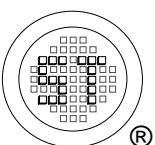
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

DFN1006-2H



UNIT	A	A1	b	D	E	e	L	R
mm	0.51	0.05	0.55	1.075	0.675	0.4	0.3	0.15
	0.46	0	0.45	0.95	0.55		0.2	0.05



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Dated: 07/05/2013 Rev: 02